

1. General description

Planar passivated high commutation three quadrant triac in a SOT428 (DPAK) surface mountable plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface mountable package
- Triggering in three quadrants only

3. Applications

- Electronic thermostats
- General purpose motor controls

4. Quick reference data

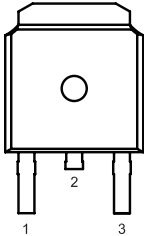

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	65	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	72	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7	-	-	10	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7	-	-	10	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 9	-	-	25	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	-	1.65	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 110\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM} ; exponential waveform; gate open circuit)	60	-	-	V/ μ s
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 0.1\text{ V}/\mu\text{s}$; gate open circuit	10	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 125\text{ °C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit; Fig. 12	5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		 sym037
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA208S-600E	TO252	BTA208S-600E,118	Reel	2500	TO252N	07-Mar-2025
					TO252Q	05-Mar-2025

Type number	Marking codes	
	Assembly factory: N	Assembly factory: Q
BTA208S-600E	208S6E PJNxxxx xx	208S6E PJQxxxx xx

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	65	A
		full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$	-	72	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	21	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 20\text{ mA}$	-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$

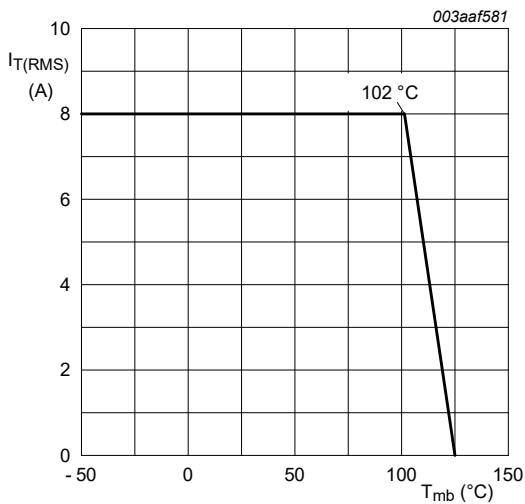


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

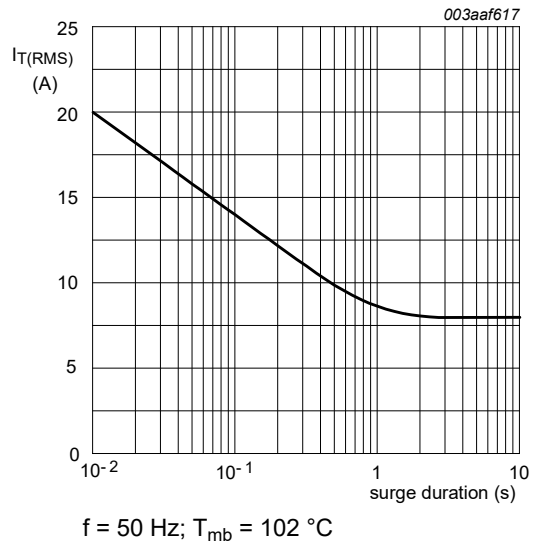


Fig. 2. RMS on-state current as a function of surge duration; maximum values

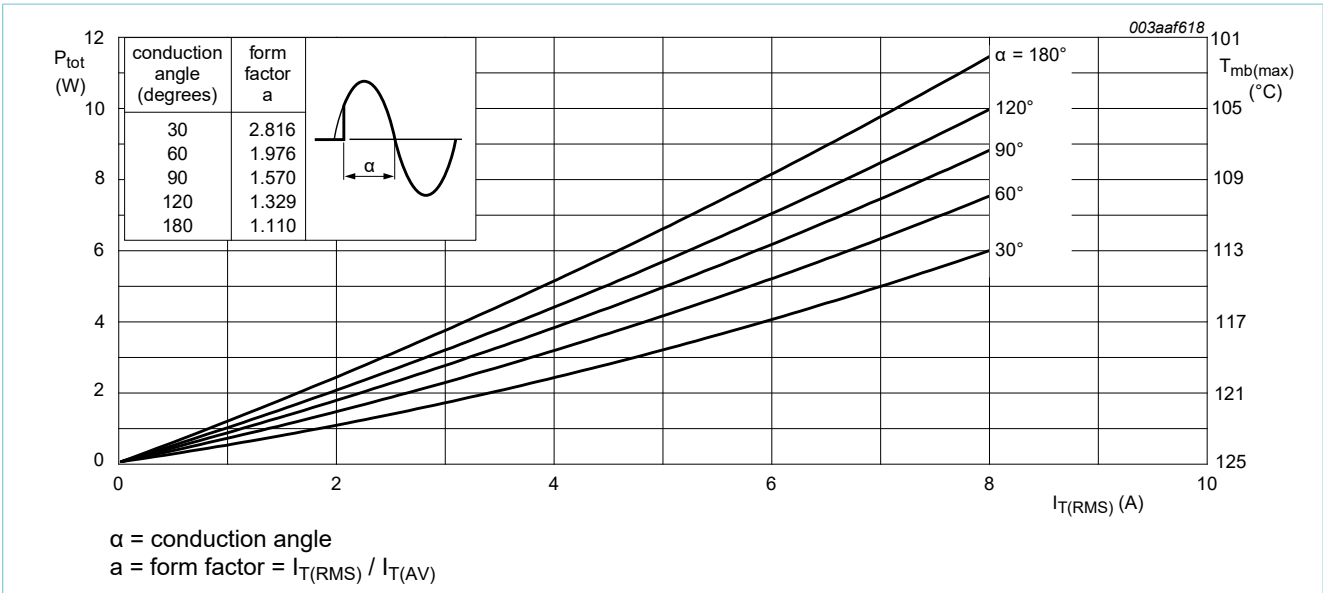


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

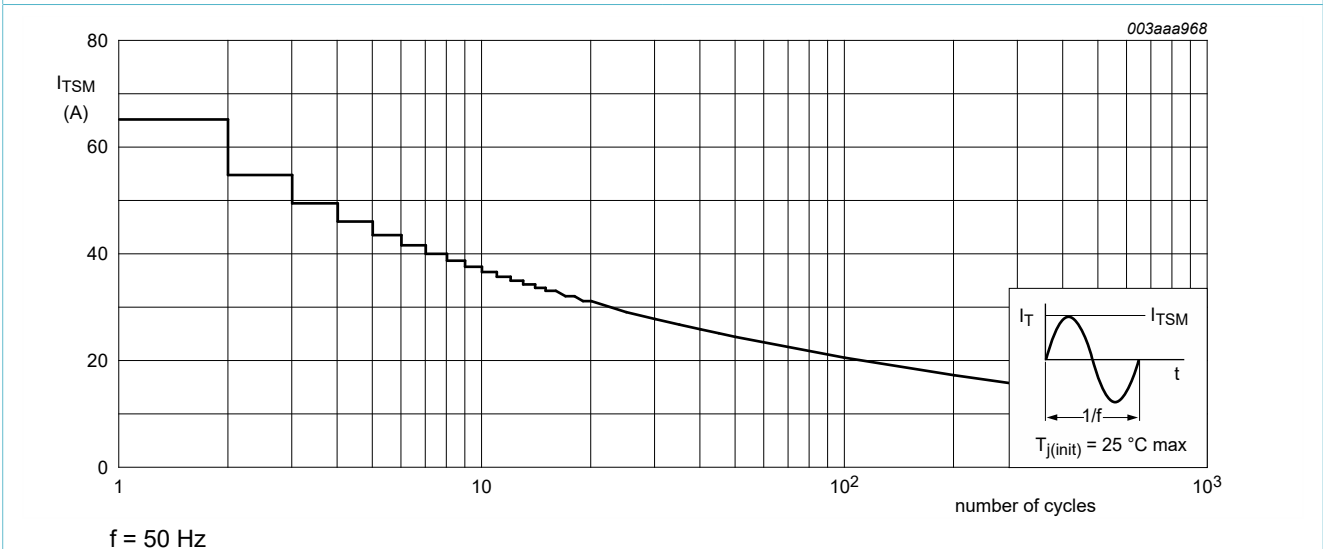
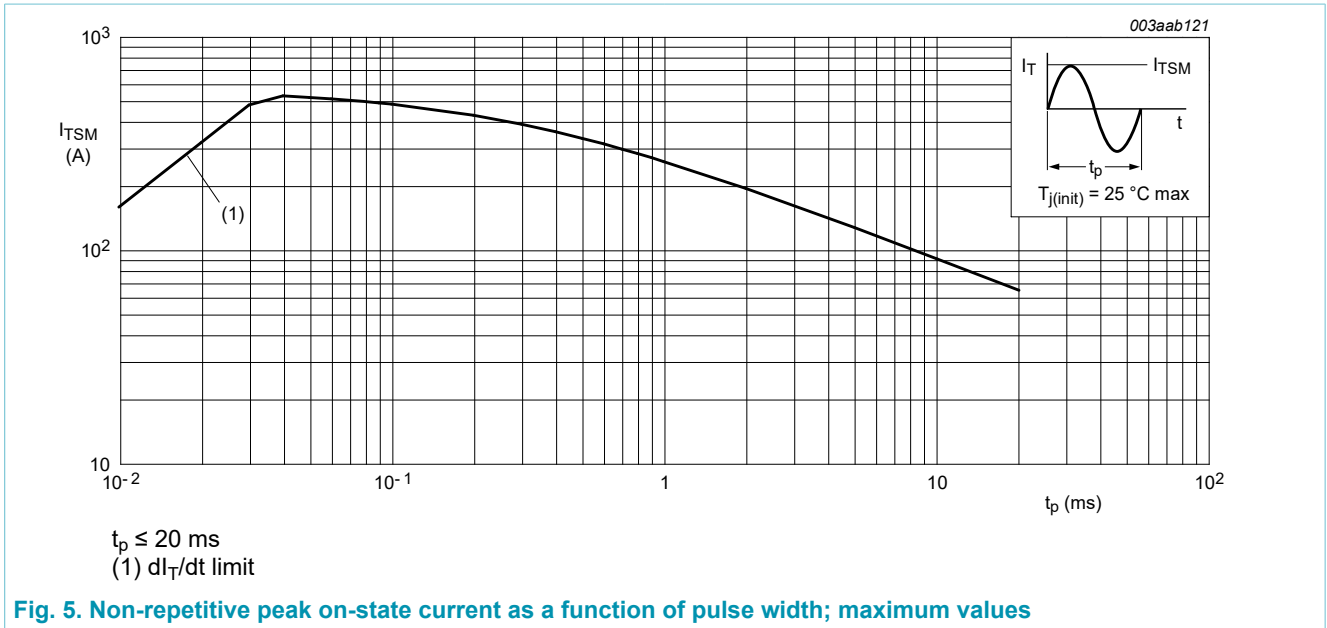


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	2	K/W
		half cycle; Fig. 6	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	75	-	K/W

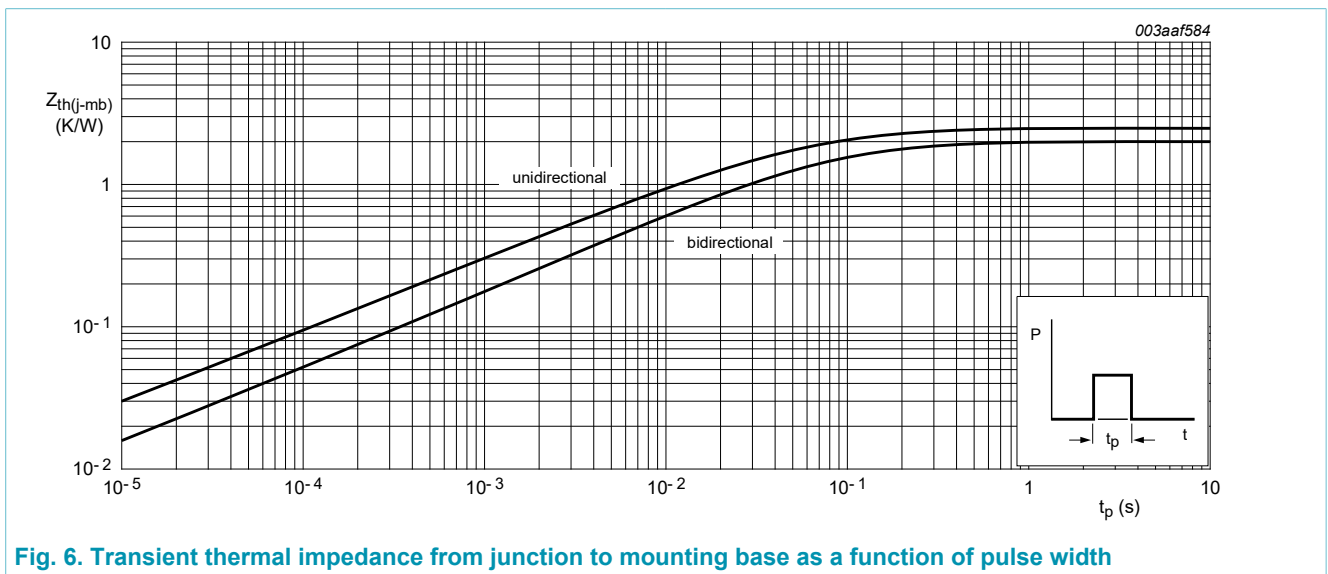
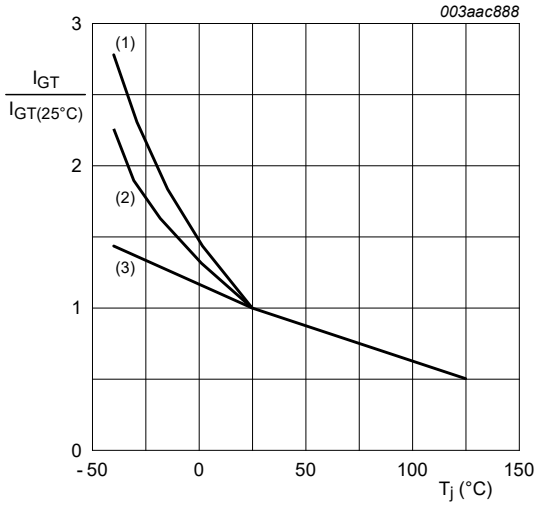


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7	-	-	10	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8	-	-	25	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8	-	-	25	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8	-	-	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9	-	-	25	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; Fig. 10	-	-	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	-	0.5	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 110 °C; (V _{DM} = 67% of V _{DRM} ; exponential waveform; gate open circuit	60	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 0.1 V/μs; gate open circuit	10	-	-	A/ms
		V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 10 V/μs; gate open circuit; Fig. 12	5	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

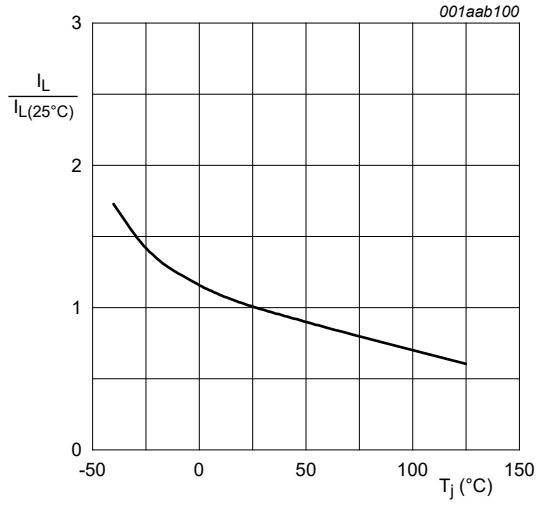


Fig. 8. Normalized latching current as a function of junction temperature

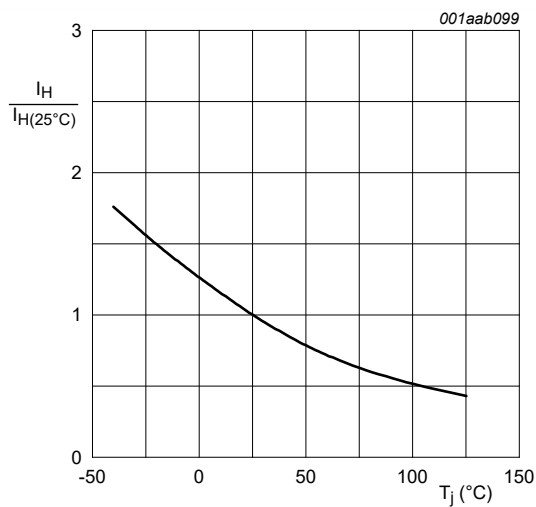
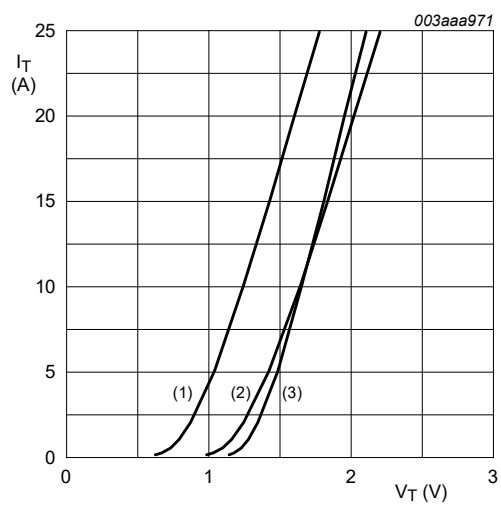
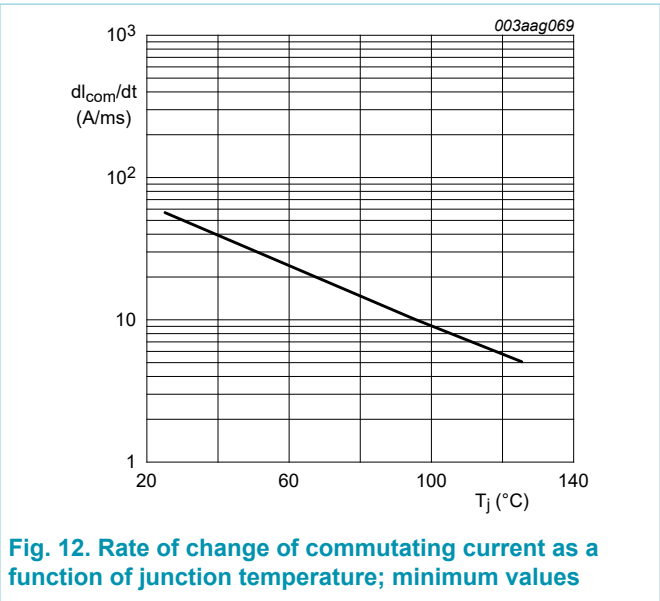
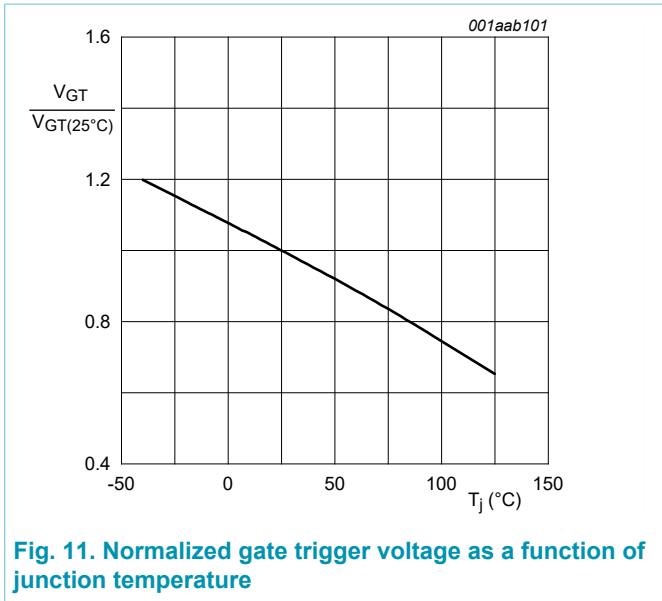


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.264 \text{ V}; R_s = 0.0378 \ \Omega$
- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
 - (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
 - (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

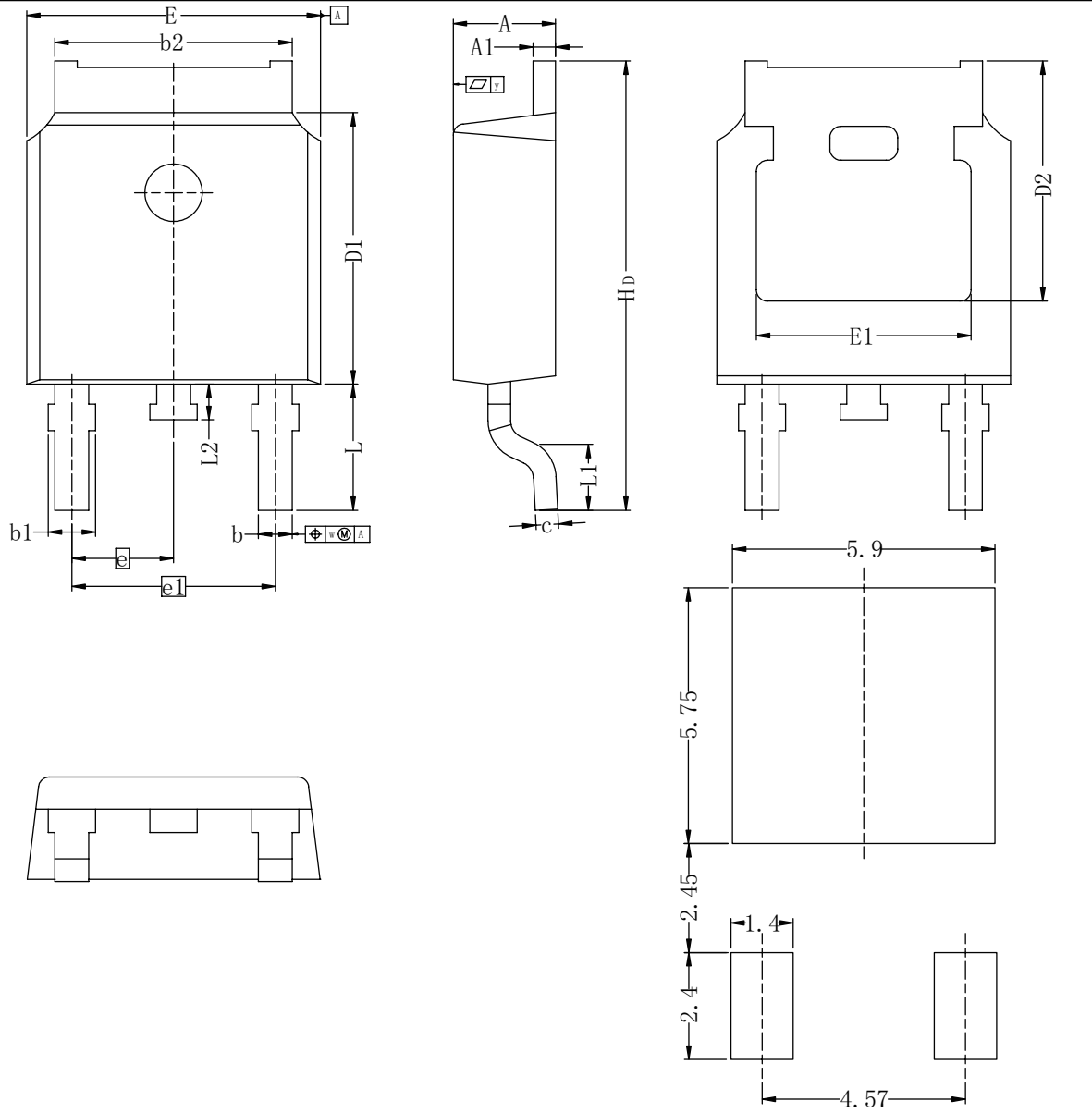
Fig. 10. On-state current as a function of on-state voltage



10. Package outline

Assembly factory: N

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)



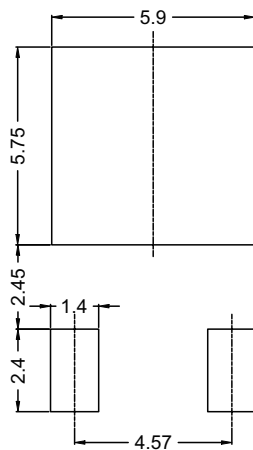
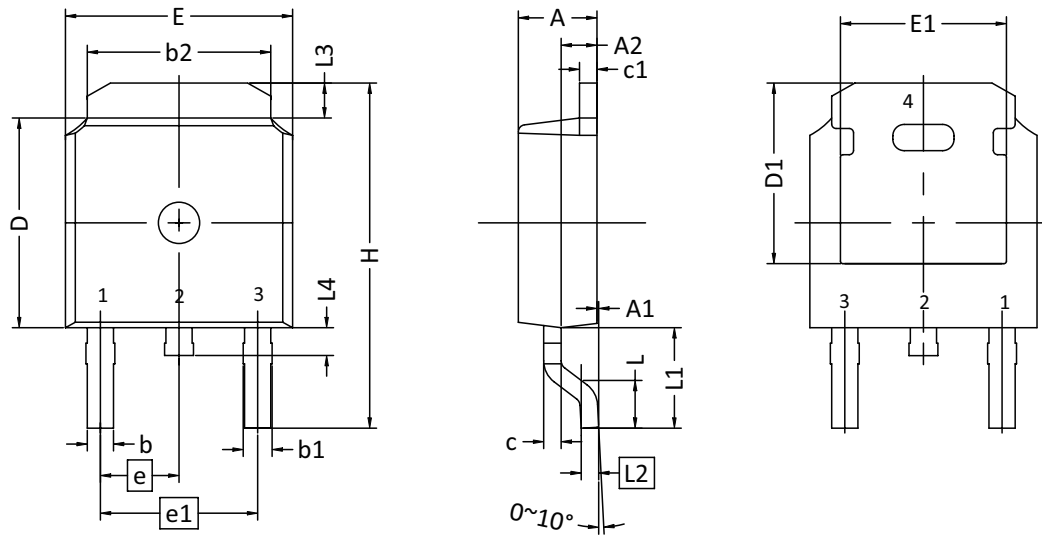
Recommended Footprint

Unit	A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H _D	L	L1	L2	w	y
min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45	2.285	4.57	9.60	2.90	0.50	0.50	0.20	0.20
nom														2.90	---	0.90		
max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40	---				

Assembly factory: Q

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252



Recommended Footprint

SYMBOLS	DIMENSION IN MM		
	MIN	NOM	MAX
A	2.184	2.286	2.400
A1	0.000	---	0.200
A2	0.889	1.041	1.170
b	0.635	0.762	0.889
b1	0.680	0.840	1.143
b2	4.953	5.340	5.500
c	0.450	0.508	0.610
c1	0.450	0.508	0.630
D	5.969	6.096	6.223
D1	5.210	5.249	5.380
E	6.350	6.604	6.800
E1	4.318	4.826	4.920
e	2.286BSC		
e1	4.572BSC		
H	9.398	10.033	10.500
L	1.270	1.520	2.032
L1	2.921REF		
L2	0.408	0.508	0.608
L3	0.889	1.016	1.270
L4	0.600	---	1.016

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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